

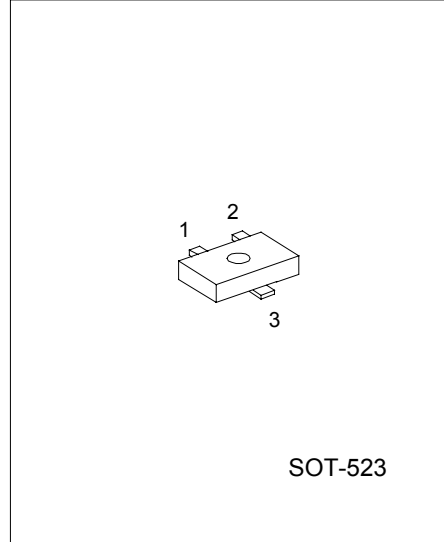
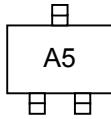
# UTC 2SA1774 PNP EPITAXIAL SILICON TRANSISTOR

## GENERAL PURPOSE TRANSISTOR

### FEATURES

- \* Excellent  $h_{FE}$  linearity
- \* Complements the UTC 2SC4617

### MARKING



1: EMITTER 2: BASE 3: COLLECTOR

### ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	$V_{CBO}$	-60	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Collector Current	$I_C$	-0.15	A
Collector Power Dissipation	$P_C$	0.15	W
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55 ~ +150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = -50\mu A$	-60			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = -1mA$	-50			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = -50\mu A$	-6			V
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = -60V$			-0.1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = -6V$			-0.1	$\mu A$
DC Current Transfer Ratio	$h_{FE}$	$V_{CE} = -6V, I_C = -1mA$	120		560	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-0.5	V
Transition Frequency	$f_T$	$V_{CE} = -12V, I_E = 2mA, f = 100MHz$		140		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = -12V, I_E = 0A, f = 1MHz$		4.0	5.0	pF

### CLASSIFICATION OF HFE1

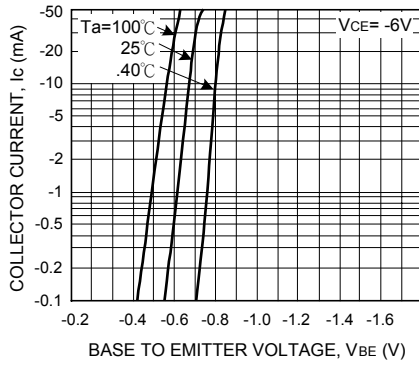
RANK	Q	R	S
Range	120 ~ 270	180 ~ 390	270 ~ 560

**UTC** UNISONIC TECHNOLOGIES CO., LTD. 1

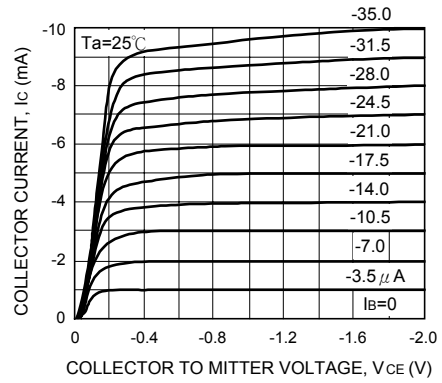
# UTC2SA1774 PNP EPITAXIAL SILICON TRANSISTOR

## ELECTRICAL CHARACTERISTICS CURVES

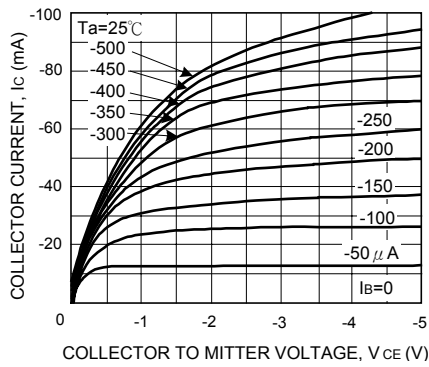
Grounded emitter propagation characteristics



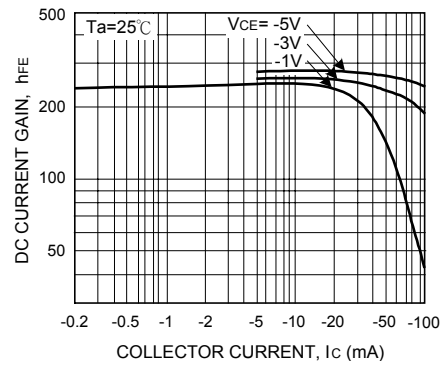
Grounded emitter output characteristics (I)



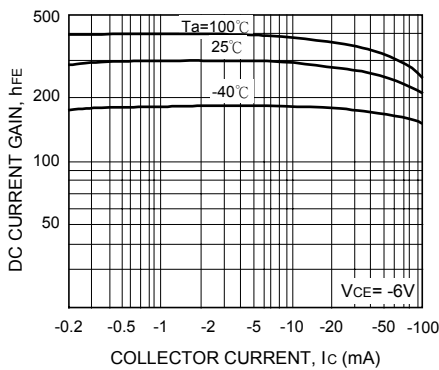
Grounded emitter output characteristics (II)



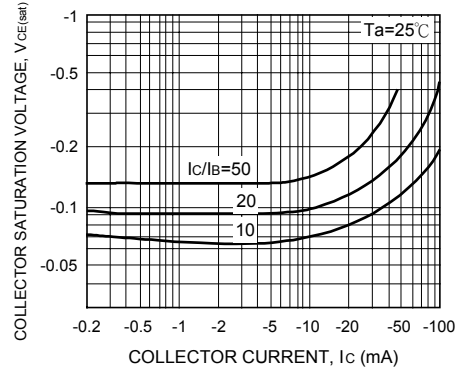
DC current gain vs. collector current (I)



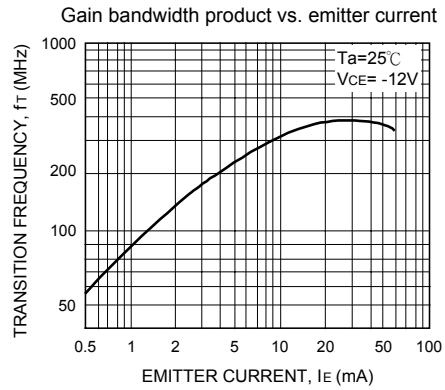
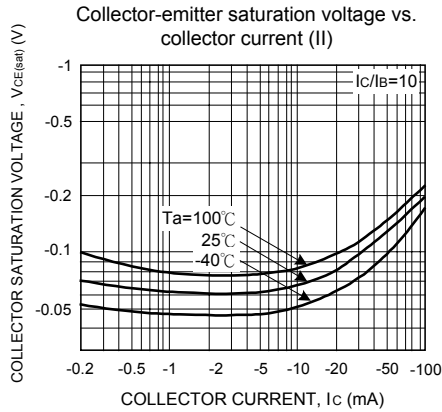
DC current gain vs. collector current (II)



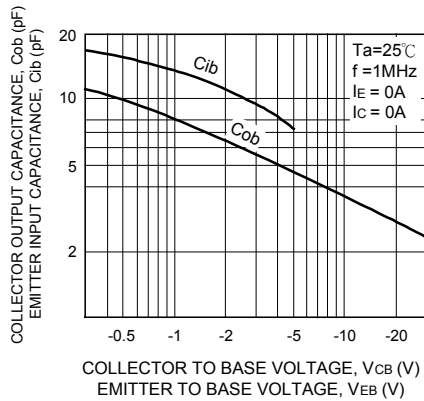
Collector-emitter saturation voltage vs. collector current (I)



# UTC 2SA1774 PNP EPITAXIAL SILICON TRANSISTOR



Collector output capacitance vs. collector-base voltage  
 Emitter input capacitance vs. emitter-base voltage



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.